## UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

: 7,023,025 B2

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APPLICATION NO.: 10/765100

**DATED** INVENTOR(S) : April 4, 2006 : Johngeon Shin

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 4, claim 1, line 3 thereof: "a first nitride layer" should read --a first nitride buffer layer--

Signed and Sealed this

Eighteenth Day of December, 2007

JON W. DUDAS Director of the United States Patent and Trademark Office